## James Gibbon

## List of Publications by Year in descending order

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933447 1125743 14 370 10 13 citations h-index g-index papers 14 14 14 753 docs citations times ranked citing authors all docs

| #  | Article   | IF   | CITATIONS |
|----|---|------|-----------|
| 1  | Chemical Control of the Dimensionality of the Octahedral Network of Solar Absorbers from the Cul–Agl–Bil <sub>3</sub> Phase Space by Synthesis of 3D CuAgBil <sub>5</sub> . Inorganic Chemistry, 2021, 60, 18154-18167. | 4.0  | 15        |
| 2  | (Invited) Band Line-up of High-k Oxides on GaN. ECS Transactions, 2020, 97, 67-81.  | 0.5  | 2         |
| 3  | Defect limitations in Cu2ZnSn(S, Se)4 solar cells utilizing an In2S3 buffer layer. Journal of Applied Physics, 2020, 127, .   | 2.5  | 15        |
| 4  | Properties of Transition Metal Dichalcogenides. , 2019, , 69-106.   |      | 3         |
| 5  | Band Alignments, Band Gap, Core Levels, and Valence Band States in Cu <sub>3</sub> BiS <sub>3</sub> for Photovoltaics. ACS Applied Materials & Interfaces, 2019, 11, 27033-27047.                                       | 8.0  | 37        |
| 6  | Transition from electron accumulation to depletion at $\hat{l}^2$ -Ga2O3 surfaces: The role of hydrogen and the charge neutrality level. APL Materials, 2019, 7, .  | 5.1  | 62        |
| 7  | Lowâ€Temperature Waferâ€Scale Deposition of Continuous 2D SnS <sub>2</sub> Films. Small, 2018, 14, e1800547.  | 10.0 | 48        |
| 8  | Band alignments at Ga2O3 heterojunction interfaces with Si and Ge. AIP Advances, 2018, 8, .   | 1.3  | 16        |
| 9  | Band gap temperature-dependence and exciton-like state in copper antimony sulphide, CuSbS2. APL<br>Materials, 2018, 6, .  | 5.1  | 14        |
| 10 | Schottky Diodes on ZnO Thin Films Grown by Plasma-Enhanced Atomic Layer Deposition. IEEE Transactions on Electron Devices, 2017, 64, 1225-1230.   | 3.0  | 8         |
| 11 | Experimental band alignment of Ta2O5/GaN for MIS-HEMT applications. Microelectronic Engineering, 2017, 178, 178-181.  | 2.4  | 8         |
| 12 | The role of nitrogen doping in ALD Ta2O5 and its influence on multilevel cell switching in RRAM. Applied Physics Letters, 2017, 110, .  | 3.3  | 54        |
| 13 | Enhanced switching stability in Ta2O5 resistive RAM by fluorine doping. Applied Physics Letters, 2017, 111, .   | 3.3  | 21        |
| 14 | Core Levels, Band Alignments, and Valence-Band States in CuSbS <sub>2</sub> for Solar Cell Applications. ACS Applied Materials & Interfaces, 2017, 9, 41916-41926.  | 8.0  | 67        |